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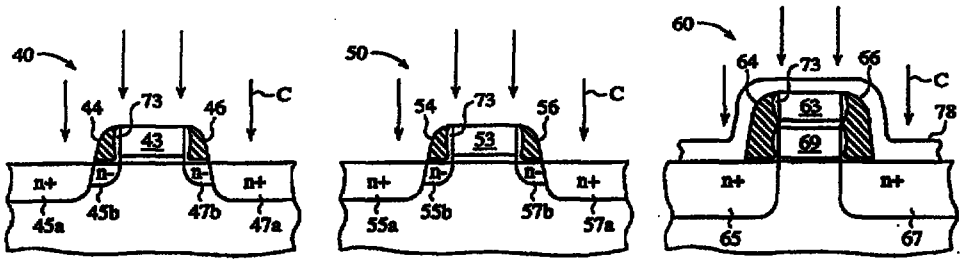
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(57) Abstract

A process for fabricating a floating gate memory cell (60) with reduced charge leakage. An oxide regrowth (73) is formed over the sides of the floating gate (69) and is then covered with an oxide protective coating (64, 66). The structure is applicable to salicide and non-salicide memory cells and is especially useful in floating gate memory cells with gate stacks having abnormally shaped side walls.